PROCESS CP361R

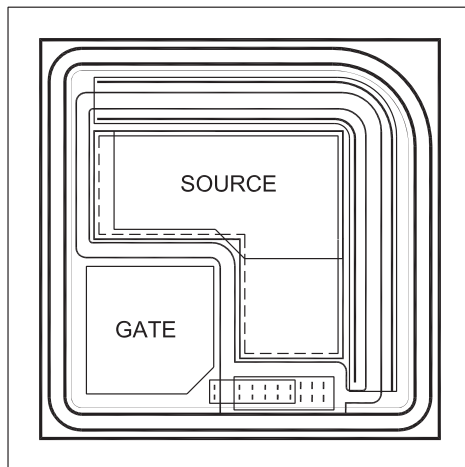
Small Signal MOSFET

N-Channel Enhancement-Mode MOSFET Chip

PROCESS DETAILS

Die Size	14.2 x 14.2 MILS
Die Thickness	3.9 MILS
Gate Bonding Pad Area	3.94 x 3.94 MILS
Source Bonding Pad Area	3.94 x 7.08 MILS
Top Side Metalization	Al-Si - 30,000Å
Back Side Metalization	Au - 12,000Å

GEOMETRY



BACKSIDE DRAIN R1

GROSS DIE PER 6 INCH WAFER
123,000

PRINCIPAL DEVICE TYPES
CEDM7001
CMNDM7001

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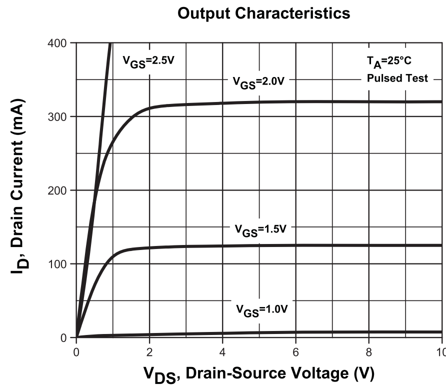
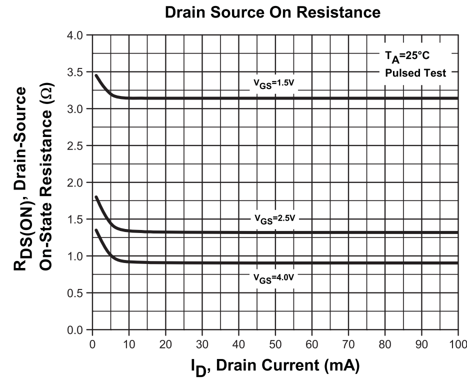
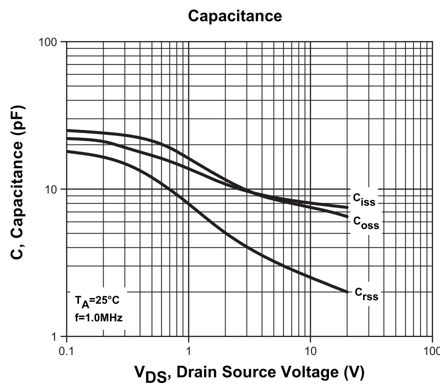
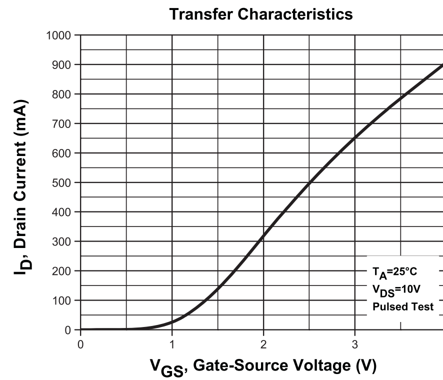
PROCESS CP361R

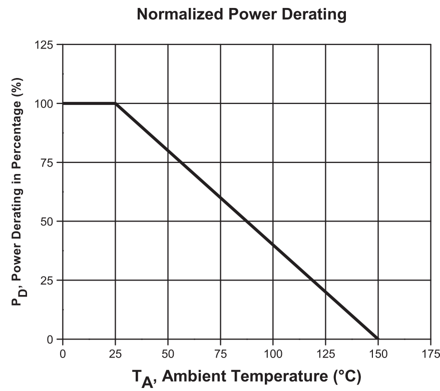
Typical Electrical Characteristics











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